



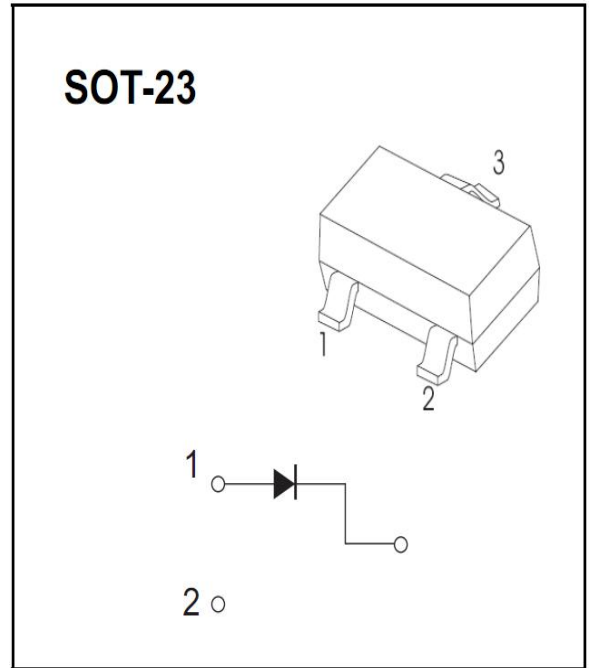
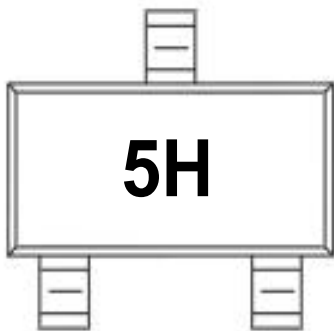
MMBD4148

Switching Diodes

FEATURES:

- High Conductance
- Fast Switching Speed
- For General Purpose Switching Applications

MARKING:



Solid dot = Green molding compound device, if none,the normal device.

Maximum ratings (@Ta=25°C)

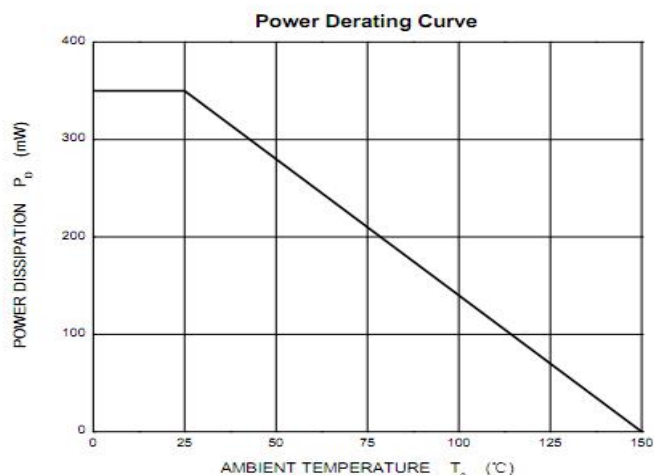
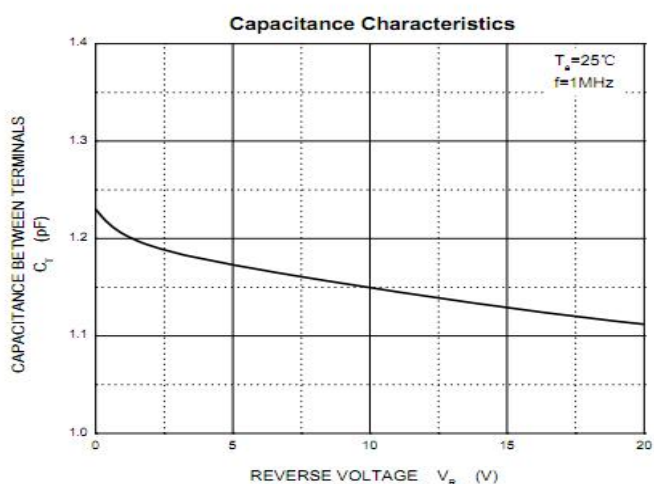
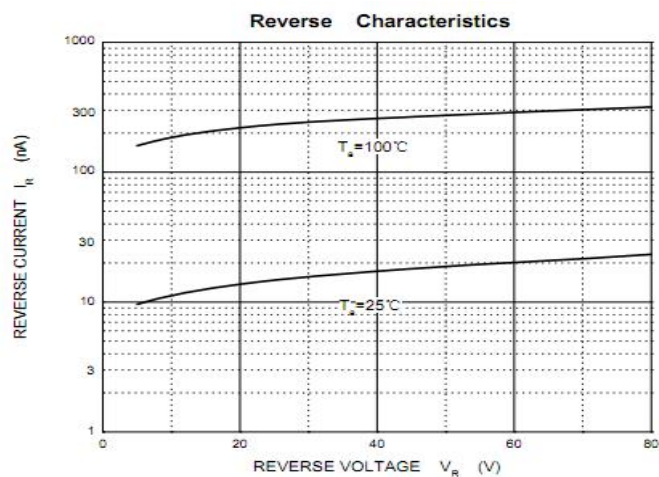
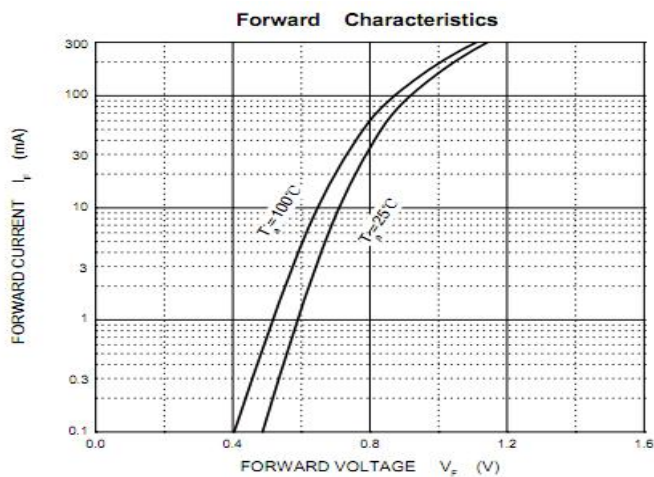
Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	VRM	100	V
Peak Repetitive Peak Reverse Voltage	VRRM	75	V
Working Peak Reverse Voltage	VRWM	75	V
DC Blocking Voltage	VR	75	V
RMS Reverse Voltage	VR(RMS)	53	V
Forward Continuous Current	IFM	300	mA
Average Rectified Output Current	Io	150	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	IFSM	2.0	A
Power Dissipation	PD	350	mW
Thermal Resistance from Junction to Ambient	RθJA	357	°C/W
Junction Temperature	TJ	150	°C
Storage Temperature Range	TSTG	-55~+150	°C



Electrical ratings (@Ta=25°C )

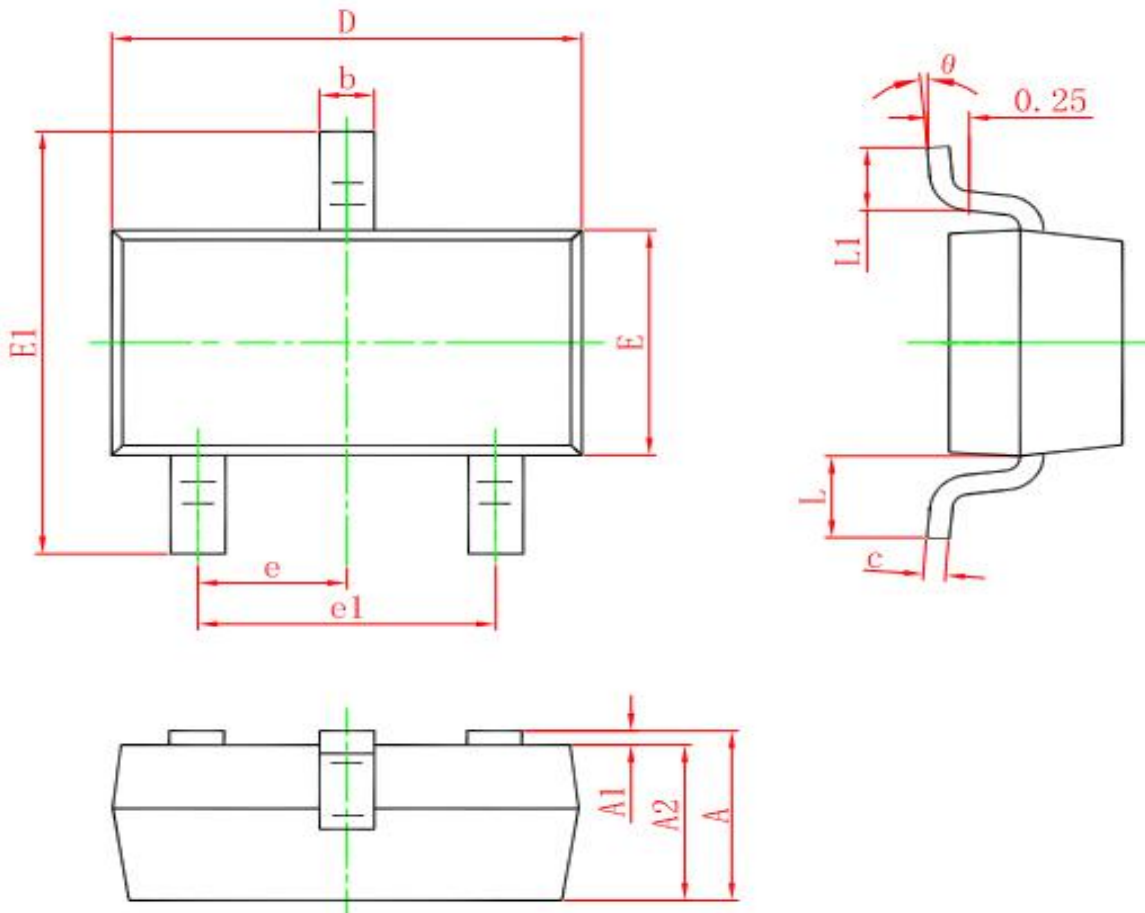
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse breakdown voltage	V(BR)1	IR=100μA	75			V
Forward voltage	VF1	IF=1mA			0.72	V
	VF2	IF=10mA			0.9	V
Reverse current	IR1	VR=75V			2.5	uA
	IR2	VR=20V			25	nA
Capacitance between terminals	Ctot	VR=0V,f=1MHz			2	PF
Reverse recovery time	t <sub>rr</sub>	IF=IR=10mA,VR=6V I <sub>rr</sub> =0.1×IR,RL= 100 Ω			4	nS

Typical Characteristics





SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°